

MOSFET – Dual, P-Channel, POWERTRENCH[®]

-20 V, -3.7 A, 72 mΩ

FDMA1023PZ

General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features two independent P-Channel MOSFETs with low on-state resistance for minimum conduction losses. When connected in the typical common source configuration, bi-directional current flow is possible.

The MicroFET 2x2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.

Features

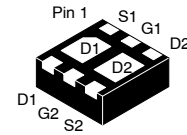
- Max $R_{DS(on)}$ = 72 mΩ at $V_{GS} = -4.5$ V, $I_D = -3.7$ A
- Max $R_{DS(on)}$ = 95 mΩ at $V_{GS} = -2.5$ V, $I_D = -3.2$ A
- Max $R_{DS(on)}$ = 130 mΩ at $V_{GS} = -1.8$ V, $I_D = -2.0$ A
- Max $R_{DS(on)}$ = 195 mΩ at $V_{GS} = -1.5$ V, $I_D = -1.0$ A
- Low Profile – 0.8 mm Maximum – In the New Package MicroFET 2x2 mm
- HBM ESD Protection Level > 2 kV (Note 3)
- Free from Halogenated Compounds and Antimony Oxides
- This Device is Pb-Free, Halide Free and is RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	±8	V
I_D	Drain Current –Continuous (Note 1a) –Pulsed	-3.7 -6	A
P_D	Power Dissipation (Note 1a) (Note 1b)	1.5 0.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

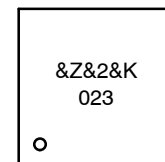
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
-20 V	72 mΩ @ -4.5 V	-3.7 A
	95 mΩ @ -2.5 V	
	130 mΩ @ -1.8 V	
	195 mΩ @ -1.5 V	



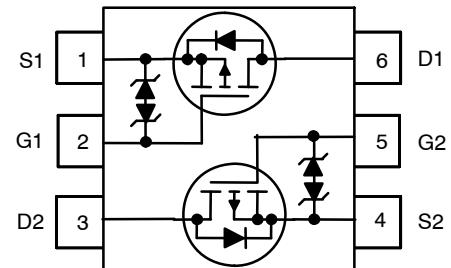
**WDFN6 2x2, 0.65P
(MicroFET 2x2)
CASE 511DA**

MARKING DIAGRAM



&Z = Assembly Plant Code
 &2 = 2-Digit Date Code
 &K = 2-Digits Lot Run Traceability Code
 023 = Device Code

PIN CONNECTIONS



ORDERING INFORMATION

Device	Package	Shipping [†]
FDMA1023PZ	WDFN6 (Pb-Free, Halide Free)	3000 / Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](http://www.onsemi.com/BRD8011/D).

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance for Single Operation, Junction to Ambient (Note 1a)	86	°C/W
$R_{\theta JA}$	Thermal Resistance for Single Operation, Junction to Ambient (Note 1b)	173	
$R_{\theta JA}$	Thermal Resistance for Dual Operation, Junction to Ambient (Note 1c)	69	
$R_{\theta JA}$	Thermal Resistance for Dual Operation, Junction to Ambient (Note 1d)	151	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain–Source Breakdown Voltage	$I_D = -250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	-20	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, referenced to 25°C	-	-11	-	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	-	-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\ \text{V}$, $V_{DS} = 0\ \text{V}$	-	-	± 10	μA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$I_D = -250\ \mu\text{A}$, $V_{GS} = V_{DS}$	-0.4	-0.7	-1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, referenced to 25°C	-	2.5	-	mV/°C
$R_{DS(on)}$	Static Drain to Source On–Resistance	$V_{GS} = -4.5\ \text{V}$, $I_D = -3.7\ \text{A}$	-	60	72	m Ω
		$V_{GS} = -2.5\ \text{V}$, $I_D = -3.2\ \text{A}$	-	75	95	
		$V_{GS} = -1.8\ \text{V}$, $I_D = -2.0\ \text{A}$	-	100	130	
		$V_{GS} = -1.5\ \text{V}$, $I_D = -1.0\ \text{A}$	-	130	195	
		$V_{GS} = -4.5\ \text{V}$, $I_D = -3.7\ \text{A}$, $T_J = 125^\circ\text{C}$	-	81	91	
g_{FS}	Forward Transconductance	$I_D = -3.7\ \text{A}$, $V_{DS} = -5\ \text{V}$	-	12	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = -10\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	490	655	pF
C_{oss}	Output Capacitance		-	100	135	pF
C_{rss}	Reverse Transfer Capacitance		-	90	135	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\ \text{V}$, $I_D = -1\ \text{A}$ $V_{GS} = -4.5\ \text{V}$, $R_{GEN} = 6\ \Omega$	-	9	18	ns
t_r	Rise Time		-	12	22	ns
$t_{d(off)}$	Turn–Off Delay Time		-	64	103	ns
t_f	Fall Time		-	37	60	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{DD} = -10\ \text{V}$, $I_D = -3.7\ \text{A}$, $V_{GS} = -4.5\ \text{V}$	-	8.6	12	nC
Q_{gs}	Gate to Source Gate Charge		-	0.7	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	2.0	-	nC

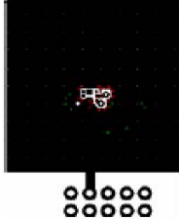
SWITCHING CHARACTERISTICS

I _S	Maximum Continuous Source–Drain Diode Forward Current		–	–	–1.1	A
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = –1.1 A (Note 2)	–	–0.8	–1.2	V
t _{rr}	Reverse Recovery Time	I _F = –3.7 A, di/dt = 100 A/μs	–	32	48	ns
Q _{rr}	Reverse Recovery Charge		–	15	23	nC

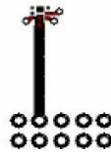
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
 - a. $R_{\theta JA} = 86^{\circ}\text{C/W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB. For single operation.
 - b. $R_{\theta JA} = 173^{\circ}\text{C/W}$ when mounted on a minimum pad of 2 oz copper. For single operation.
 - c. $R_{\theta JA} = 69^{\circ}\text{C/W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB. For dual operation.
 - d. $R_{\theta JA} = 151^{\circ}\text{C/W}$ when mounted on a minimum pad of 2 oz copper. For dual operation.



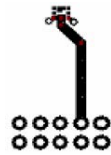
a. 86°C/W when mounted on a 1 in² pad of 2 oz copper.



b. 173°C/W when mounted on a minimum pad of 2 oz copper.



c. 69°C/W when mounted on a 1 in² pad of 2 oz copper.



d. 151°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

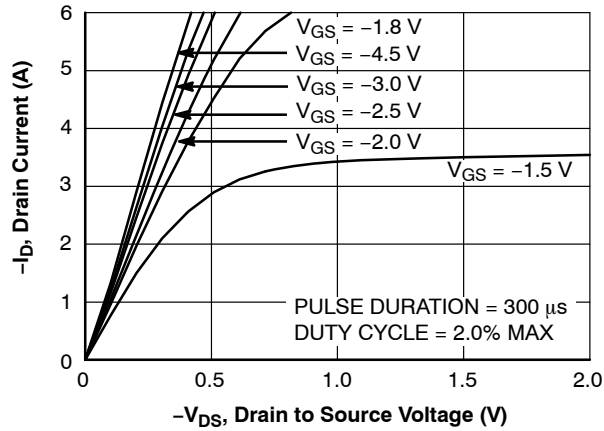
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Figure 1. On-Region Characteristics

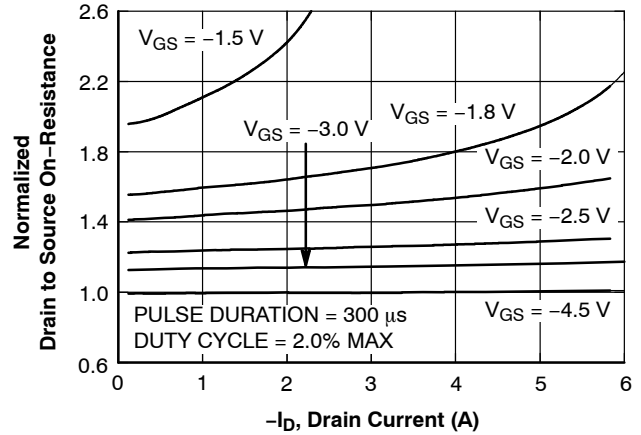


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

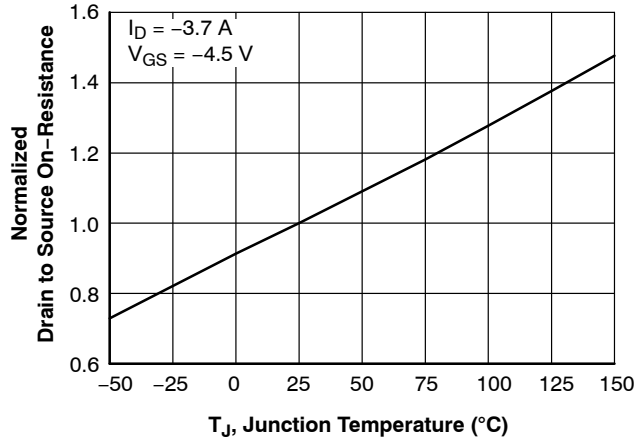


Figure 3. Normalized On-Resistance vs. Junction Temperature

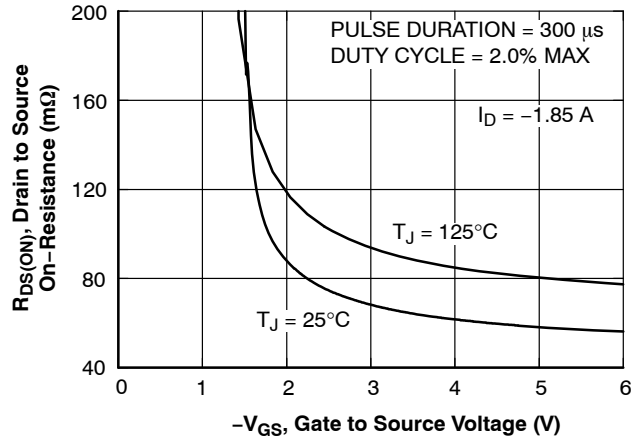


Figure 4. On-Resistance vs. Gate to Source Voltage

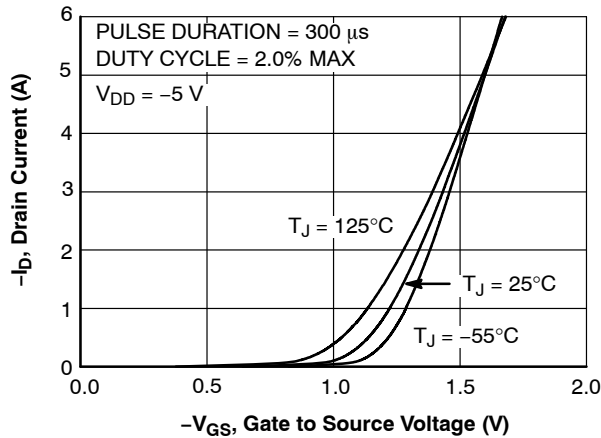


Figure 5. Transfer Characteristics

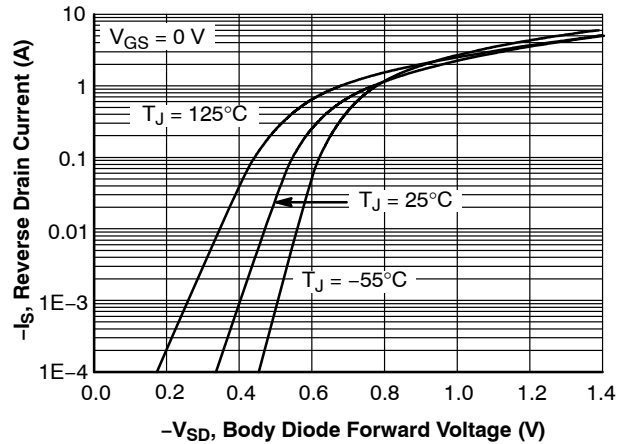


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

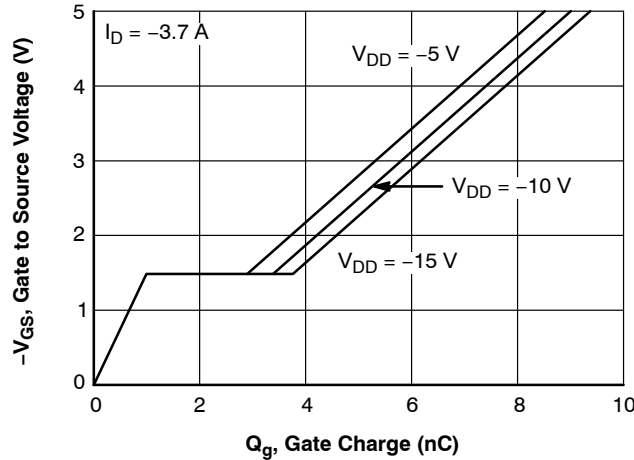
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Figure 7. Gate Charge Characteristics

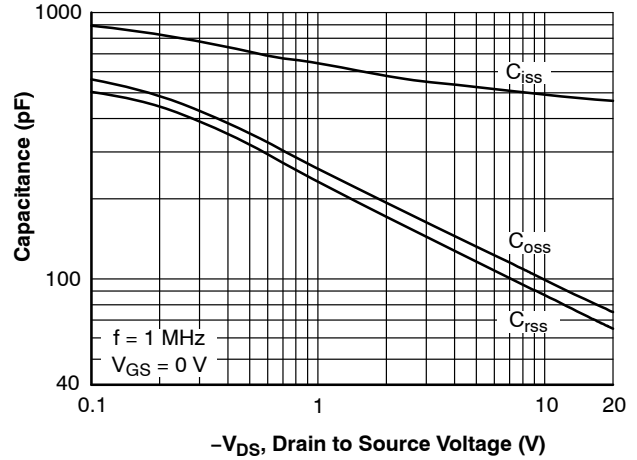


Figure 8. Capacitance Characteristics

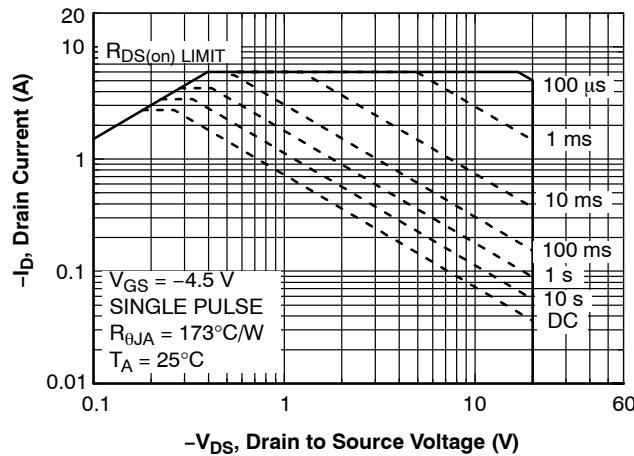


Figure 9. Forward Bias Safe Operating Area

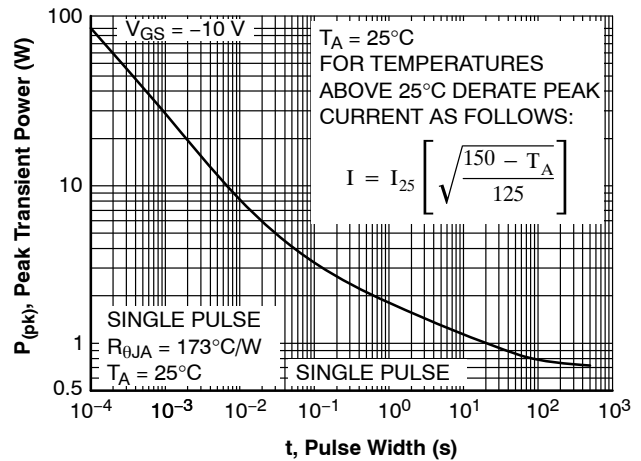


Figure 10. Single Pulse Maximum Power Dissipation

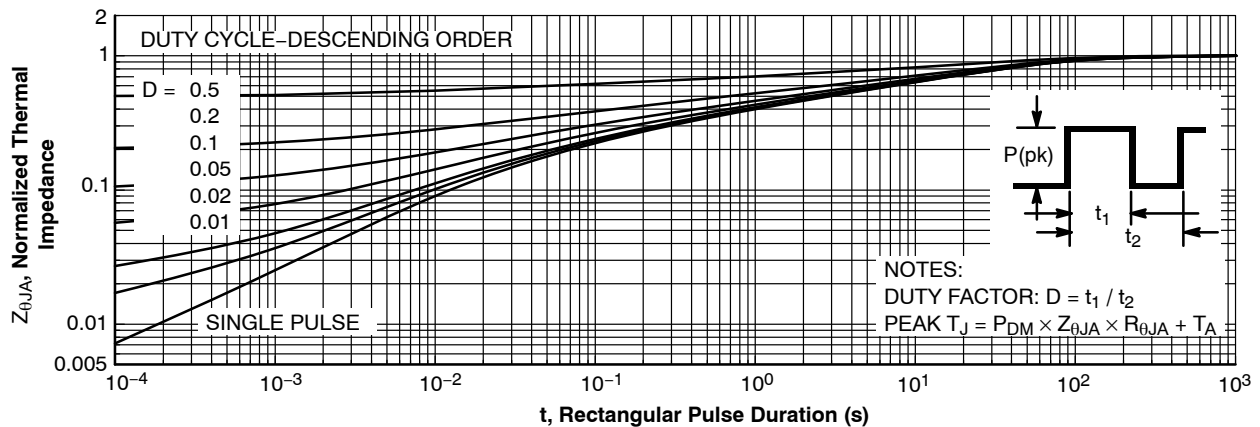


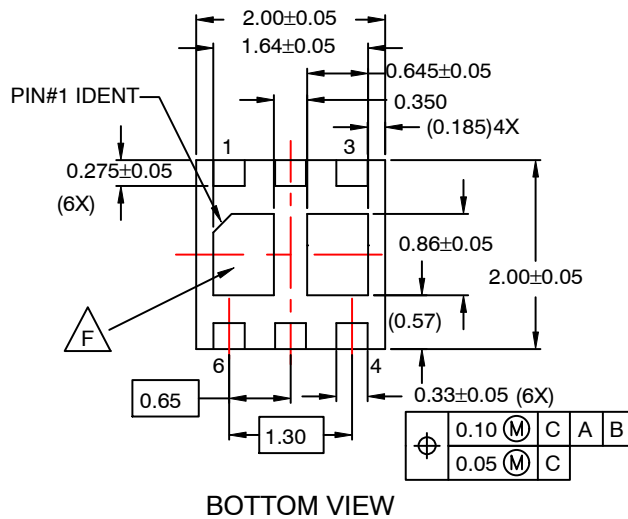
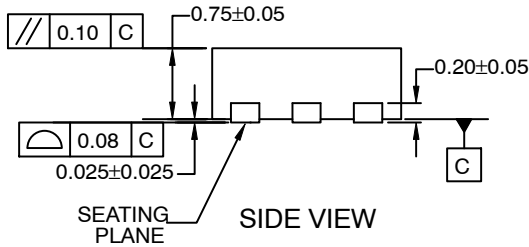
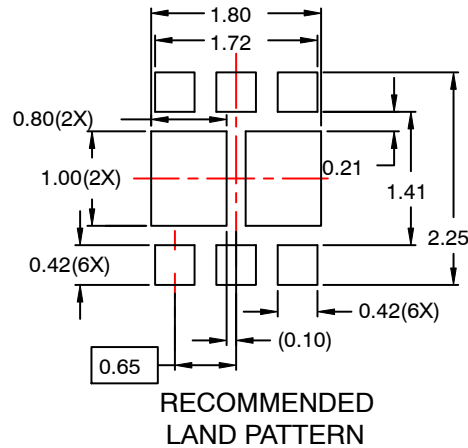
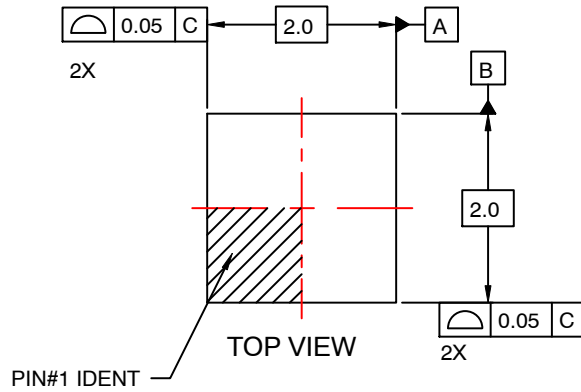
Figure 11. Transient Thermal Response Curve

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WDFN6 2x2, 0.65P
CASE 511DA
ISSUE O

DATE 31 JUL 2016



NOTES:

- CONFORM TO JEDEC REGISTRATIONS MO-229, VARIATION VCCC, EXCEPT WHERE NOTED.
- DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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